

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 3, line 13, as follows:

--FIG. 1 is a diagram illustrating an exemplary magnetic memory device. In FIG. 1, magnetic memory device 100, which may be used, for example, as a magnetic storage element in a magnetic random access memory (MRAM) device, comprises magnetic layers 102 and 106 separated by a non-magnetic layer 104. In a typical magnetic memory device, e.g., magnetic memory device 100, one of magnetic layers 102 and 106 has a fixed magnetization (hereinafter referred to as the "fixed layer"), while the other of magnetic layers 102 and 106 has a variable magnetization that may be switched (hereinafter referred to as the "free layer" which may comprise one or more free magnetic layers and at least one non-magnetic layer between the one or more free magnetic layers). Magnetic memory device 100 may comprise, for example, a magnetic tunnel junction (MTJ) device.--